

CMOS Digital Integrated Circuits Silicon Monolithic

74HC4538D

1. Functional Description

· Dual Monostable Multivibrator

2. General

The 74HC4538D is a high speed CMOS MONOSTABLE MULTIVIBRATOR fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

There are two trigger inputs, A input (positive edge input), and \overline{B} input (negative edge input). These inputs are valid for a slow rise/fall time signal ($t_r = t_f = 1$ s) as they are schmitt trigger inputs.

After triggering, the output stays in a MONOSTABLE state for the time period determined by the external resistor and capacitor (R_X , C_X). A low level at \overline{CD} input breaks this STABLE STATE. In the MONOSTABLE state, if a new trigger is applied, it makes the MONOSTABLE period longer (retrigger mode).

Limitations for C_X and R_X are as follows:

External capacitor C_XNo limitation

External resistor $R_X.....V_{\rm CC}$ = 2.0 V more than 5 $k\Omega$

 V_{CC} = 3.0 V more than 1 k Ω

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

3. Features (Note)

- (1) High speed: tpd = 25 ns (typ.) at $V_{CC} = 5 \text{ V}$
- (2) Low power dissipation:

Standby state: $I_{CC} = 4.0 \mu A \text{ (max)}$ at $T_a = 25 \text{ °C}$

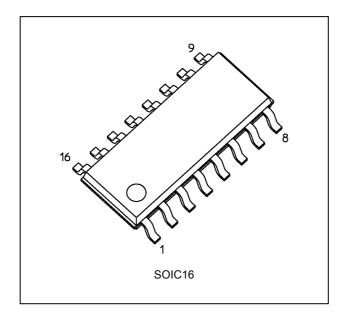
Active state: $I_{CC} = 350 \mu A \text{ (max)}$ at $T_a = 25 \text{ °C}$

- (3) Balanced propagation delays: t_{PLH} ≈ t_{PHL}
- (4) Wide operating voltage range: $V_{CC(opr)} = 2.0$ to 6.0 V

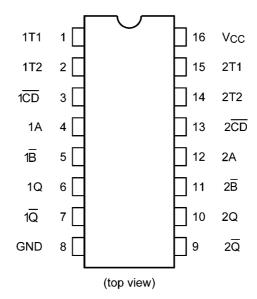
Note: In the case of using only one circuit, $\overline{\text{CD}}$ should be tied to GND, $\text{T1} \cdot \text{T2} \cdot \text{Q} \cdot \overline{\text{Q}}$ should be tied to OPEN, the other inputs should be tied to V_{CC} or GND.



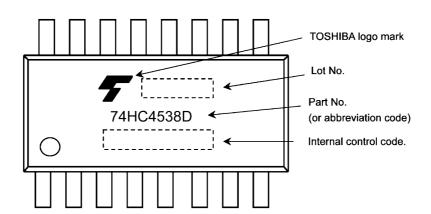
4. Packaging



5. Pin Assignment

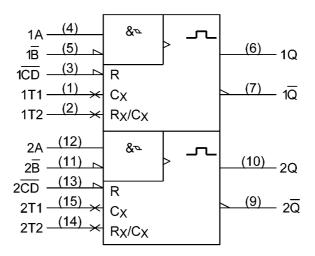


6. Marking





7. IEC Logic Symbol



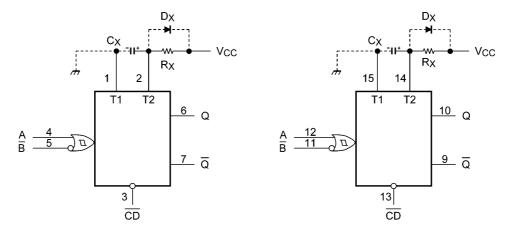
8. Truth Table

	Inputs		Out	puts	Note
Α	B	CD	Q	Q	Note
	Н	Н	Л		Output Enable
Х	L	Н	L	Н	Inhibit
Н	Х	Н	L	Н	Inhibit
L		Н	Л		Output Enable
Х	Х	L	L	H	Reset

X: Don't care



9. Block Diagram



- C_X, R_X, D_X are external Capacitor, resistor, and diode, respectively.
- (2) External clamping diode, D_X;

The external capacitor is charged to V_{CC} level in the wait state, i.e. when no trigger is applied. Supply voltage is turned off and C_X is discharged mainly through the internal (parasitic) diode. If C_X is sufficiently large and V_{CC} drops rapidly, there will be some possibility of damaging the IC by rush current or latch-up. If the capacitance of the supply voltage filter is large enough and V_{CC} drops slowly, the rush current is automatically limited and damage to the IC is avoided.

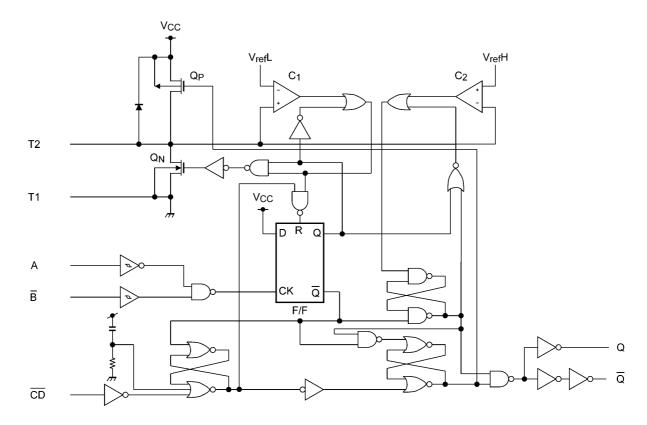
The maximum value of forward current through the parasitic diode is ±20 mA.

In the case of a large C_X , the limitation of fall time of the supply voltage is determined as follows: $t_f \ge (V_{CC}$ - 0.7) $C_X/20$ mA

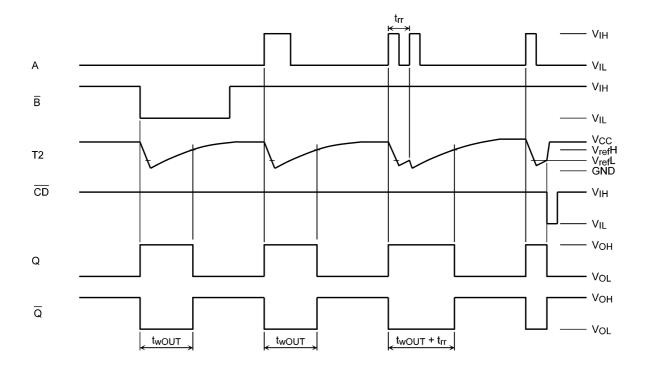
 $(t_f$ is the time from the voltage supply turning off to the level of supply voltage reaching 0.4 V_{CC} .) In the care of a system that does not satisfy the above condition, an external clamping diode is needed to protect the IC from rush current.



10. System Diagram



11. Timing Chart



Rev.6.0



12. Functional Description

(1) Stand-by state

The external capacitor is fully charge to V_{CC} in the stand-by state. That means, before triggering, Q_P and Q_N transistors which are connected to the T2 node are in the off state. Two comparators that relate to the timing of the output pulse, and two reference voltage supplies stop their operation. The total supply current is only leakage current.

(2) Trigger operation

Trigger operation is effective in either of the following two cases. One is the condition where the A input is low, and the \overline{B} input has a falling signal. The other, where the \overline{B} input is high, and the A input has a rising signal.

After trigger becomes effective, comparators C_1 and C_2 start operating, and Q_N is turned on. The external capacitor discharges through Q_N . The voltage level at the T2 node drops. If the T2 voltage level falls to the internal reference voltage $V_{ref}L$, the output of C_1 becomes low. The flip-flop is then reset and Q_N turns off. At that moment C_1 stops but C_2 continues operating.

After Q_N turns off, the voltage at T2 start rising at a rate determined by the time constant of external capacitor C_X and resistor R_X .

After the triggering, output Q becomes high, following some delay time of the internal F/F and gates. It stays high even if the voltage of T2 changes from falling to rising. When T2 reaches the internal reference voltage $V_{ref}H$, the output of C_2 becomes low, the output Q goes low and C_2 stops its operation. That means, after triggering, when the voltage level of T2 reaches $V_{ref}H$, the IC returns to its MONOSTABLE state

In the case of large value of C_X and R_X , and ignoring the discharge time of the capacitor and internal delays of the IC, the width of the output pulse, (t_{wOUT}) , is as follows:

$$t_{wOUT} = 0.7 \times C_X \times R_X$$

(3) Retrigger operation

When another new trigger is applied to input A or \overline{B} while in the MONOSTABLE state, it is effective only if the IC is charging C_X . The voltage level of T2 then falls to $V_{ref}L$ level again.

Therefore the Q output stays high if the next trigger comes in before the time period set by C_X and R_X . If the 2^{nd} trigger is very close to previous trigger, such as application during the discharge cycle, the 2^{nd} trigger will not be effective.

The minimum time for effective 2^{nd} trigger, t_{rr} (min), depends on V_{CC} and C_X .

(4) Reset operation

In normal operation, $\overline{\mathrm{CD}}$ input is held high. If $\overline{\mathrm{CD}}$ is low, a trigger has no effect because the Q output is held low and the trigger control F/F is reset. Also, Q_P turns on and C_X is charged rapidly to V_{CC} . This means if $\overline{\mathrm{CD}}$ input is set low, the IC goes into a wait state.



13. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		-0.5 to 7.0	V
Input voltage	V _{IN}		-0.5 to V _{CC} + 0.5	V
Output voltage	V _{OUT}		-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}		±20	mA
Output diode current	I _{OK}		±20	mA
Output current	I _{OUT}		±25	mA
V _{CC} /ground current	I _{CC}		±50	mA
Power dissipation	P _D	(Note 1)	500	mW
Storage temperature	T _{stg}		-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: P_D derates linearly with -8 mW/°C above 85°C.

14. Operating Ranges (Note)

Characteristics	Symbol	Note	Test Condition	Rating	Unit
Supply voltage	V _{CC}		_	2.0 to 6.0	V
Input voltage	V _{IN}		_	0 to V _{CC}	V
Output voltage	V _{OUT}			0 to V _{CC}	V
Operating temperature	T _{opr}			-40 to 125	°C
Input rise and fall times (CD only)	t _r ,t _f		V _{CC} = 4.5 V	0 to 50	μS
External capacitor	C _X	(Note 1)	_	No limitation	F
External resistor	R _X	(Note 1)	V _{CC} = 2.0 V	≥ 5 k	Ω
			$V_{CC} \ge 3.0 \text{ V}$	≥ 1 k	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

Note 1: The maximum allowable values of C_X and R_X are a function of leakage of capacitor C_X , the leakage of 74HC4538D, and leakage due to board layout and surface resistance.

Susceptibility to externally induced noise signals may occur for $R_X > 1 M\Omega$.



15. Electrical Characteristics

15.1. DC Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	n	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage	V _{IH}	_		2.0	1.50	_	_	V
				4.5	3.15	_	_	
				6.0	4.20	_	_	V
Low-level input voltage	V _{IL}	_		2.0	-	_	0.50	V
				4.5	I		1.35	
				6.0	-		1.80	V
High-level output voltage	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -20 μA	2.0	1.9	2.0		V
(Q, Q)				4.5	4.4	4.5		
				6.0	5.9	6.0		
			I _{OH} = -4 mA	4.5	4.18	4.31	_	
			I _{OH} = -5.2 mA	6.0	5.68	5.80		
Low-level output voltage	V _{OL} V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 20 μA	2.0		0.0	0.1	V
(Q, Q)				4.5		0.0	0.1	
				6.0	_	0.0	0.1	
			I _{OL} = 4 mA	4.5	_	0.17	0.26	
			I _{OL} = 5.2 mA	6.0	_	0.18	0.26	V
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND		6.0	1		±0.1	μА
T2 terminal input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND		6.0			±0.5	μΑ
Quiescent supply current	I _{CC}	$V_{IN} = V_{CC}$ or GND		6.0	1	1	4.0	μА
Active-state supply current	I _{CC(opr)}	$V_{IN} = V_{CC}$ or GND		2.0	1	40	120	μА
(per circuit)		T2 ext = 0.25 V _{CC}		4.5	1	250	350	
				6.0	_	450	600	



15.2. DC Characteristics (Unless otherwise specified, T_a = -40 to 85 °C)

Characteristics	Symbol	Test Conditio	n	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	_		2.0	1.50	_	V
				4.5	3.15	_	
				6.0	4.20	_	
Low-level input voltage	V _{IL}	_		2.0		0.50	V
				4.5	_	1.35	
				6.0	_	1.80	
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20 μA	2.0	1.9	_	V
(Q, \overline{Q})				4.5	4.4	_	
				6.0	5.9	_]
			I _{OH} = -4 mA	4.5	4.13	_]
			I _{OH} = -5.2 mA	6.0	5.63	_	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 20 μA	2.0	_	0.1	V
(Q, Q)				4.5	_	0.1	
				6.0	_	0.1	
			I _{OL} = 4 mA	4.5	_	0.33]
			I _{OL} = 5.2 mA	6.0	_	0.33	V
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND		6.0	_	±1.0	μА
T2 terminal input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	±5.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		6.0	_	40.0	μА
Active-state supply current	I _{CC(opr)}	V _{IN} = V _{CC} or GND		2.0	_	160	μА
(per circuit)		T2 ext = 0.25 V _{CC}		4.5	_	400]
				6.0	_	800	

15.3. DC Characteristics (Unless otherwise specified, T_a = -40 to 125 °C)

Characteristics	Symbol	Test Condition	n	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	_		2.0	1.50	_	V
				4.5	3.15	_	
				6.0	4.20	_	
Low-level input voltage	V _{IL}	_		2.0		0.50	V
				4.5		1.35	
				6.0		1.80	
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20 μA	2.0	1.9	_	V
(Q, Q)				4.5	4.4	_	
				6.0	5.9	_	
			I _{OH} = -4 mA	4.5	3.7	_	
			I _{OH} = -5.2 mA	6.0	5.2	_	
Low_level output voltage	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 20 μA	2.0	_	0.1	V
(Q, \overline{Q})				4.5	_	0.1	
				6.0	_	0.1	
			I _{OL} = 4 mA	4.5	_	0.4	
			I _{OL} = 5.2 mA	6.0	_	0.4	
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	±1.0	μА
T2 terminal input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	±10.0	μА
Quiescent supply current	Icc	V _{IN} = V _{CC} or GND	,	6.0	_	80.0	μА
Active-state supply current	I _{CC(opr)}	V _{IN} = V _{CC} or GND		2.0	_	160	μА
(per circuit)		T2 ext = 0.25 V _{CC}		4.5	_	400	
				6.0	_	800	



15.4. Timing Requirements (Unless otherwise specified, $T_a = 25$ °C, Input: $t_f = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Limit	Unit
Minimum pulse width	$t_{w(L)},t_{w(H)}$	_	2.0	_	75	ns
(A, \overline{B})			4.5	_	15	
			6.0	_	13	
Minimum pulse width	t _{w(L)}	_	2.0	_	75	ns
(CD)			4.5	_	15	
			6.0	_	13	
Minimum removal time	t _{rem}	_	2.0	_	25	ns
			4.5	_	5	
			6.0	_	4	
Minimum retrigger time	t _{rr}	$R_X = 1 \text{ k}\Omega, C_X = 100 \text{ pF}$	2.0	60	_	ns
			4.5	25	_	
			6.0	20	_	
		$R_X = 1 \text{ k}\Omega, C_X = 0.01 \mu\text{F}$	2.0	1.8	_	μS
			4.5	0.8	_	
			6.0	0.7	_	

15.5. Timing Requirements (Unless otherwise specified, T_a = -40 to 85 °C, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Limit	Unit
Minimum pulse width	$t_{w(L)}, t_{w(H)}$	_	2.0	95	ns
(A, \overline{B})			4.5	19	
			6.0	16	
Minimum pulse width	t _{w(L)}	_	2.0	95	ns
(CD)			4.5	19	
			6.0	16	
Minimum removal time	t _{rem}	_	2.0	30	ns
			4.5	6	
			6.0	5	

15.6. Timing Requirements (Unless otherwise specified, T_a = -40 to 125 °C, Input: t_f = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Limit	Unit
Minimum pulse width	$t_{w(L)}, t_{w(H)}$	_	2.0	110	ns
(A, \overline{B})			4.5	22	
			6.0	19	
Minimum pulse width	t _{w(L)}		2.0	135	ns
(CD)			4.5	27	
			6.0	23	
Minimum removal time	t _{rem}		2.0	40	ns
			4.5	8	
			6.0	7	



15.7. AC Characteristics (Unless otherwise specified, $C_L = 15 \text{ pF}$, $V_{CC} = 5 \text{ V}$, $T_a = 25 ^{\circ}\text{C}$, Input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	t _{TLH} ,t _{THL}	_	_	6	12	ns
Propagation delay time $(A, \overline{B} - Q, \overline{Q})$	t _{PLH} ,t _{PHL}	_	_	25	44	
Propagation delay time (CD - Q, Q)	t _{PLH} ,t _{PHL}	_	_	25	44	

15.8. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = 25 °C, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	Note	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
Output transition time	t_{TLH}, t_{THL}		_	2.0	_	30	75	ns
				4.5	_	8	15	
				6.0		7	13	
Propagation delay time	t _{PLH} ,t _{PHL}		_	2.0		120	250	ns
(A, B - Q, Q)				4.5		30	50	
				6.0		25	43	
Propagation delay time	t_{PLH}, t_{PHL}		_	2.0		120	250	ns
$(\overline{CD} - Q, \overline{Q})$				4.5	ı	30	50	
				6.0		25	43	
Output pulse width	t _{wOUT}		$C_X = 0 F$ $R_X = 5 k\Omega (V_{CC} - 2.0V)$ $R_X = 1 k\Omega (V_{CC} - 4.5 V, 6.0 V)$ $C_X = 0.01 \mu F$	2.0	_	540	1200	ns
				4.5		180	250	
				6.0		150	200	
				2.0	70	83	96	μS
			$R_X = 10 \text{ k}\Omega$	4.5	69	77	85	
				6.0	69	77	85	
			$C_X = 0.1 \mu F$	2.0	0.73	0.79	0.85	ms
			$R_X = 10 \text{ k}\Omega$	4.5	0.71	0.75	0.79	
				6.0	0.71	0.75	0.79	
Output pulse width error between circuits (in same package)	Δt_{wOUT}		_			±1		%
Input capacitance	C _{IN}		_			5	10	pF
Power dissipation capacitance	C_{PD}	(Note 1)				40	_	pF

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation.

 $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC'} \times Duty/100 + I_{CC}/2$ (per circuit),

(I_{CC}: Active supply current),

(Duty: %)



15.9. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = -40 to 85 °C, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Output transition time	t _{TLH} ,t _{THL}	_	2.0	_	95	ns
			4.5	_	19	
			6.0	_	16	1 I
Propagation delay time	t _{PLH} ,t _{PHL}	_	2.0	_	315	ns
$(A, \overline{B} - Q, \overline{Q})$			4.5	_	63	
			6.0	_	54]
Propagation delay time	t _{PLH} ,t _{PHL}	_	2.0	_	315	ns
(CD - Q, Q)			4.5	_	63	
			6.0	_	54]
Output pulse width	t _{wOUT}	C _X = 0 F	2.0	_	1500	ns
		$R_X = 5 \text{ k}\Omega \text{ (V}_{CC} = 2.0 \text{V)}$ $R_X = 1 \text{ k}\Omega \text{ (V}_{CC} = 4.5 \text{ V}, 6.0 $	4.5	_	320	ns
		V)	6.0		260	ns
		C _X = 0.01 μF	2.0	70	96	μS
		$R_X = 10 \text{ k}\Omega$	4.5	69	85	μS
			6.0	69	85	μS
		C _X = 0.1 μF	2.0	0.71	0.86	ms
		$R_X = 10 \text{ k}\Omega$	4.5	0.70	0.80	ms
			6.0	0.70	0.80	ms
Input capacitance	C _{IN}				10	pF

15.10. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = -40 to 125 °C, Input: t_Γ = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Output transition time	t _{TLH} ,t _{THL}	_	2.0	_	110	ns
			4.5	_	22	
			6.0	_	19	
Propagation delay time (A, B - Q, Q)	t _{PLH} ,t _{PHL}	_	2.0	_	380	ns
			4.5	_	76	1 1
			6.0	_	65	
Propagation delay time (CD - Q, Q)	t _{PLH} ,t _{PHL}	_	2.0	_	380	ns
			4.5	_	76	
			6.0	_	65	
Output pulse width	t _{wout}	C_X = 0 F R_X = 5 k Ω (V _{CC} = 2.0V) R_X = 1 k Ω (V _{CC} = 4.5 V, 6.0 V)	2.0	_	1500	ns
			4.5	_	320	
			6.0	_	260	1
		$C_X = 0.01 \mu\text{F}$ $R_X = 10 \text{k}\Omega$	2.0	70	96	μS
			4.5	69	85	
			6.0	69	85	1 1
		$C_X = 0.1 \mu F$ $R_X = 10 kΩ$	2.0	0.71	0.87	ms
			4.5	0.70	0.81	
			6.0	0.70	0.81	



16. Characteristics Curves (Note)

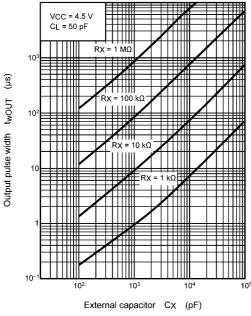


Fig. 16.1 t_{WOUT} - C_X (typ.)

Fig. 16.2 t_{rr} - V_{CC} (typ.)

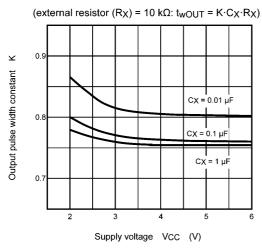


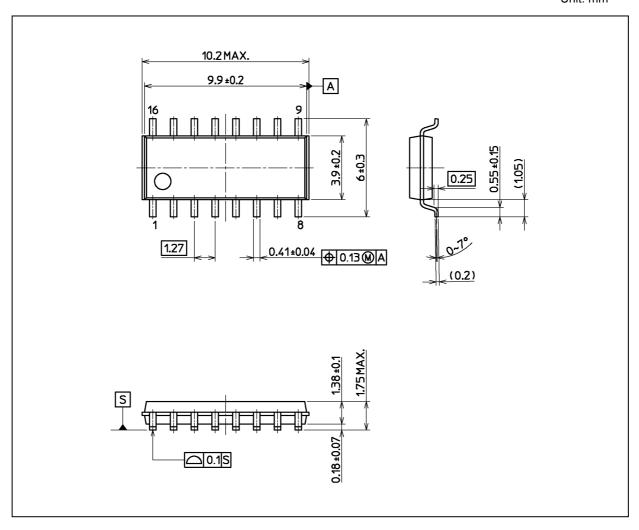
Fig. 16.3 Output Pulse Width Constant K - Supply Voltage (typ.)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.15 g (typ.)

	Package Name(s)
Nickname: SOIC16	



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